

2SB1048

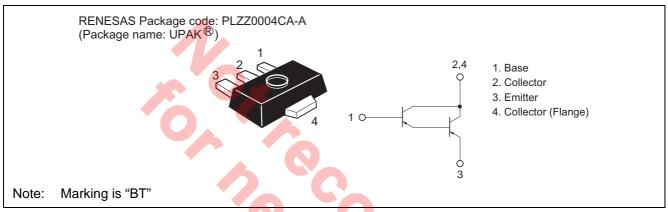
Silicon PNP Epitaxial, Darlington

REJ03G0665-0200 (Previous ADE-208-1040) Rev.2.00 Aug.10.2005

Application

High gain amplifier

Outline



*UPAK is a trademark of Renesas Technology Corp.

Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	-60	V
Collector to emitter voltage	V _{CEO}	-60	V
Emitter to base voltage	V_{EBO}	-7	V
Collector current	Ι _C	-1	Α
Collector peak current	i _{C(peak)} *1	-2	Α
Collector power dissipation	Pc*2	1	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW \leq 10 ms, Duty cycle \leq 20%

2. Value on the alumina ceramic board (12.5 \times 30 \times 0.7 mm)

Electrical Characteristics

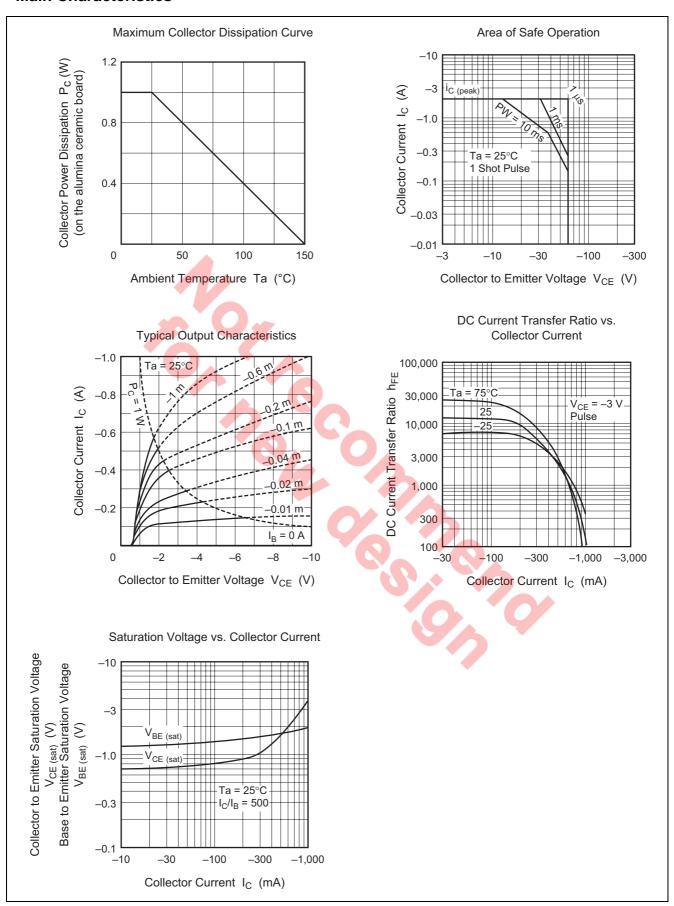
 $(Ta = 25^{\circ}C)$

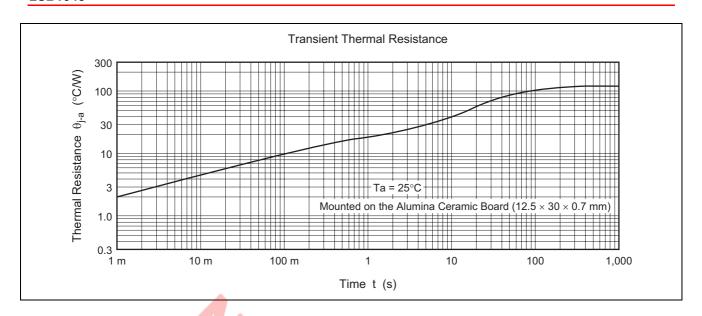
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	-60	_	_	V	$I_C = -10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-60	_	_	V	$I_C = -1 \text{ mA}, R_{BE} = \infty$
Collector cutoff current	I _{CBO}	_	_	-10	μΑ	$V_{CB} = -60 \text{ V}, I_E = 0$
Emitter cutoff current	I _{EBO}	_	_	-10	μΑ	$V_{EB} = -7 \text{ V}, I_{E} = 0$
DC current transfer ratio	h _{FE}	2000	_	100000		$V_{CE} = -3 \text{ V}, I_{C} = -500 \text{ mA*}^{1}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	_	_	-2.0	V	$I_C = -500 \text{ mA}, I_B = -1 \text{ mA*}^1$
Base to emitter saturation voltage	$V_{BE(sat)}$	_	_	-2.0	V	$I_C = -500 \text{ mA}, I_B = -1 \text{ mA*}^1$

Notes: 1. Pulse test



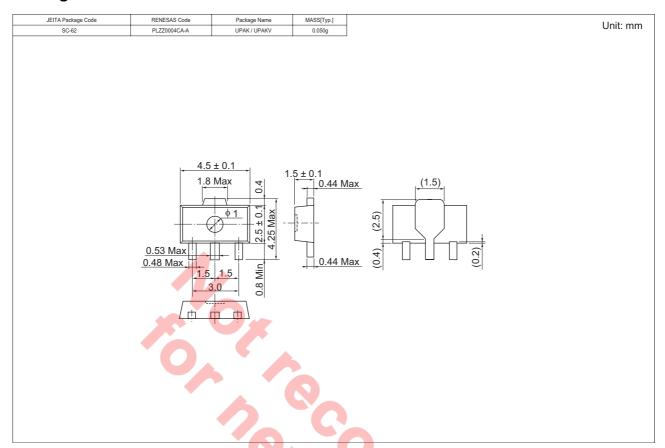
Main Characteristics







Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
2SB1048BTTR-E	1000	φ 178 mm Reel, 12 mm Emboss Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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